

CEU703AL-VB Datasheet

N-Channel 30-V (D-S) MOSFET

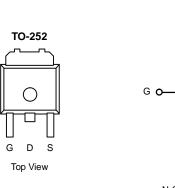
FEA	TU	RE	S

- Trench Power MOSFET •
- 100 % Rg and UIS Tested ٠
- Compliant to RoHS Directive 2011/65/EU

APPLICATIONS

- OR-ing
- Server
- DC/DC

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Тур)		
30	0.007 at V _{GS} = 10 V	70	25 nC		
30	0.009 at V _{GS} = 4.5 V	60	20110		



N-Channel MOSFET

D

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted) Symbol Parameter Limit V_{DS} Drain-Source Voltage 30 V_{GS} Gate-Source Voltage ± 20 T_C = 25 °C 70 T_C = 70 °C 50 Continuous Drain Current (T_J = 175 °C) I_D T_A = 25 °C 21.8^{b, c} T_A = 70 °C 18^{b, c} Pulsed Drain Current I_{DM} 200 Avalanche Current Pulse I_{AS} 39 L = 0.1 mHSingle Pulse Avalanche Energy E_{AS} 94.8 T_C = 25 °C 50^{a, e} Continuous Source-Drain Diode Current I_S T_A = 25 °C 3.13^{b, c} T_C = 25 °C 100^a T_C = 70 °C 75 Maximum Power Dissipation P_D $T_A = 25 \degree C$ 3.25^{b, c} $T_A = 70 \degree C$ 2.33^{b, c}

Operating Junction and Storage Temperature Range T_J, T_{stg}

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	$t \le 10 \text{ sec}$	R _{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	0,00	

Notes:

a. Based on T_C = 25 °C. b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 sec.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

COMPLIANT

Unit

V

А

mJ

А

W

°C

- 55 to 175



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$ 30				V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		m)//9C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$		- 7.5		mV/°0
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.5		2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	90			Α
		V _{GS} = 10 V, I _D = 21.8 A		0.007		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 18A		0.009		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 21.8 A		160		S
Dynamic ^b						
Input Capacitance	C _{iss}			2201		pF
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		525		
Reverse Transfer Capacitance	C _{rss}			370		
Total Gate Charge	Q _g	V_{DS} = 15 V, V_{GS} = 10 V, I_{D} = 21.8 A	35	45	1	
				25	35	
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 21.8 A		15		nC
Gate-Drain Charge	Q _{gd}			20		
Gate Resistance	Rg	f = 1 MHz			2.1	Ω
Turn-On Delay Time	t _{d(on)}			18	27	1
Rise Time	t _r	V_{DD} = 15 V, R _L = 0.625 Ω		11	17	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_{\text{D}}\cong$ 24 A, V_{GEN} = 10 V, R_{g} = 1 Ω		70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}			55	83	ns
Rise Time	t _r	V_{DD} = 15 V, R _L = 0.67 Ω		180	270	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 22.5 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			120	
Pulse Diode Forward Current ^a	I _{SM}			1	120	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		27		
Reverse Recovery Rise Time	t _b			25		ns

Notes:

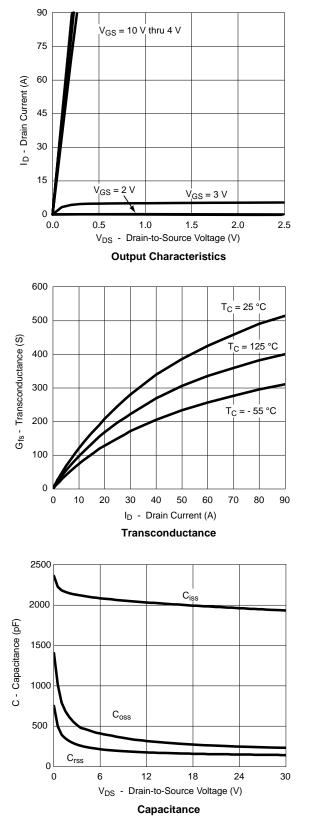
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle ≤ 2 %.

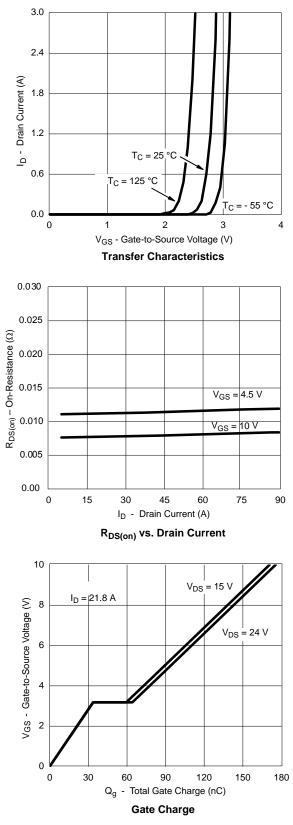
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



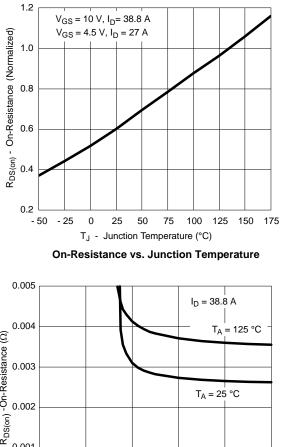


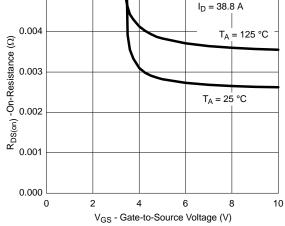


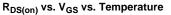


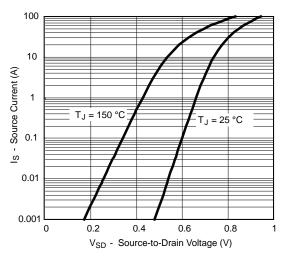


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

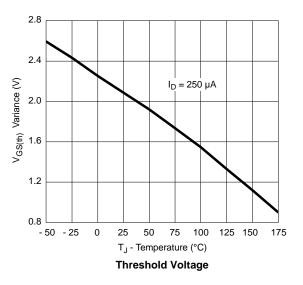


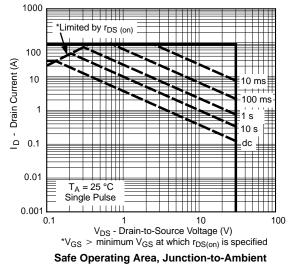




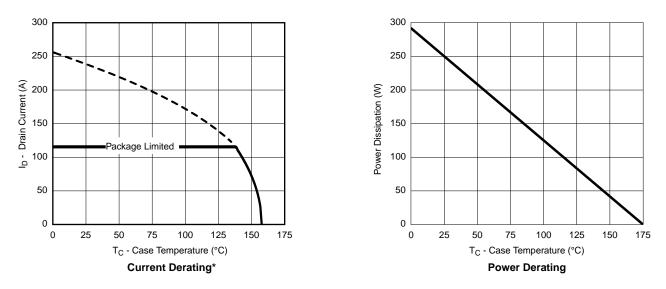


Forward Diode Voltage vs. Temperature









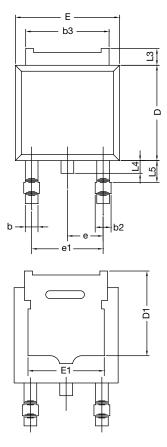
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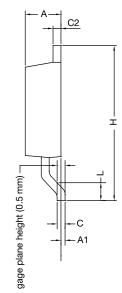
*The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





TO-252AA CASE OUTLINE





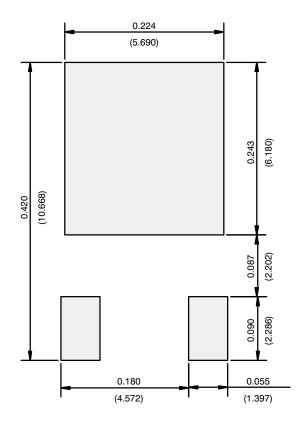
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	0.090 BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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